

## **isc** Silicon NPN Power Transistor

## 2SC2516

### DESCRIPTION

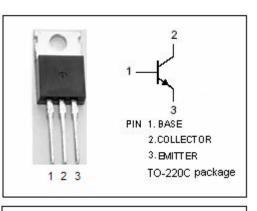
- Low Collector Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

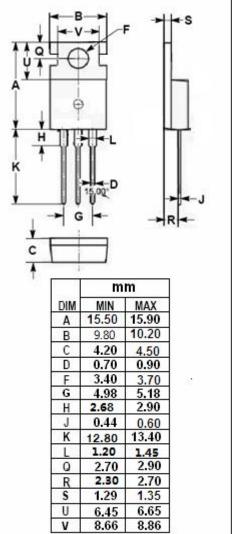
### **APPLICATIONS**

• Designed for high-speed switching, and is ideal for use as a driver in devices such as switching reglators,DC/DC converters, and high frequency power amplifiers.

#### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	80	V
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	12	V
Ι <sub>C</sub>	Collector Current-Continuous	5	А
Ісм	Collector Current-Peak	10	А
I <sub>B</sub>	Base Current-Continuous	2.5	А
Pc	Collector Power Dissipation @ T <sub>a</sub> =25℃	1.5	14/
	Total Power Dissipation @ T <sub>C</sub> =25℃	30	W
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C





isc website: www.iscsemi.com



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## ELECTRICAL CHARACTERISTICS

## $T_{c}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ; I <sub>B</sub> = 0	60		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	Ic= 3.0A; I <sub>B</sub> = 0.3A		0.6	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3.0A; I <sub>B</sub> = 0.3A		1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 60V; I <sub>E</sub> = 0		10	μA
I <sub>CER</sub>	Collector Cutoff Current	V <sub>CE</sub> = 60V; R <sub>BE</sub> = 51 Ω , T <sub>a</sub> =125°C		1.0	mA
I <sub>CEX</sub>	Collector Cutoff Current	$\label{eq:Vce} \begin{array}{l} V_{CE} = 60V; \ V_{BE(off)} = -1.5V \\ V_{CE} = 60V; \ V_{BE(off)} = -1.5V, \ T_a = 125 \ {\rm ^{\circ}C} \end{array}$		10 1.0	μA mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> =0		10	μA
h <sub>FE-1</sub>	DC Current Gain	Ic= 0.3A; Vce= 5V	40		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3.0A; V <sub>CE</sub> = 5V	40	200	

Switching times

t <sub>on</sub>	Turn-on Time		0.5	μs
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 3.0A ,R <sub>L</sub> = 17 Ω , I <sub>B1</sub> = -I <sub>B2</sub> = 0.3A,V <sub>CC</sub> ≈ 50V	3.0	μ
t <sub>f</sub>	Fall Time		0.5	μ <b>S</b>

### h<sub>FE-2</sub> Classifications

М	L	К
40-80	60-120	100-200



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